

ABSTRACT OF THE DISCLOSURE

To improve resistance to instantaneous surge power of semiconductor devices having resistor films. The semiconductor device includes: a semiconductor substrate; a first insulating film formed on the semiconductor substrate; a polysilicon resistor film formed on the first insulating film; a second insulating film formed on the resistor film; a high heat conductor film consisting of a highly heat-conducting material formed on the second insulating film; and a pair of terminal wirings and formed on the second insulating film and connected to the resistor film, in which a thickness T_3 of the second insulating film is thinner than a thickness T_2 of the resistor film.